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STTH8003CY

HIGH FREQUENCY SECONDARY RECTIFIERS

MAJOR PRODUCTS CHARACTERISTICS

I_{F(AV)}	2x40 A
V_{RRM}	300 V
V_F (max)	1 V
t_{rr} (max)	60 ns

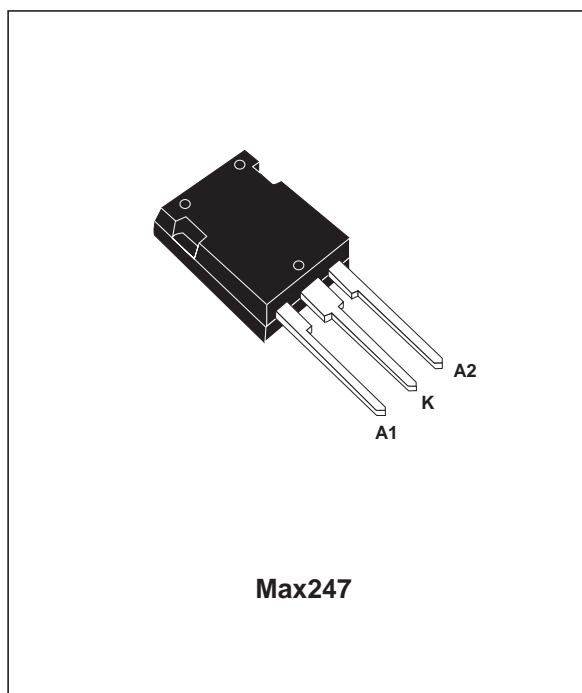
FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND VOLTAGE PERFORMANCE.
- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY.
- HIGH OPERATING TEMPERATURE THANKS TO LOW LEAKAGE CURRENT.

DESCRIPTION

Dual rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in Max247, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipment and telecom power supplies.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			300	V
I _{F(RMS)}	RMS forward current			50	A
I _{F(AV)}	Average forward current	T _c = 105°C δ = 0.5	Per diode Per device	40 80	A
I _{FSM}	Surge non repetitive forward current		t _p = 10 ms sinusoidal	400	A
I _{RSM}	Non repetitive avalanche current		t _p = 100 μs square	4	A
T _{stg}	Storage temperature range			-55 +175	°C
T _j	Maximum operating junction temperature			+ 175	°C

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case thermal resistance		0.8	°C/W
	Per diode Total		0.5	
R _{th(c)}	Coupling		0.2	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = 300 V	T _j = 25°C			80	μA
			T _j = 125°C		80	800	
V _F **	Forward voltage drop	I _F = 40 A	T _j = 25°C			1.25	V
			T _j = 125°C		0.85	1	

Pulse test : * t_p = 5 ms, δ < 2 %

** t_p = 380 μs, δ < 2%

To evaluate the maximum conduction losses use the following equation :

$$P = 0.75 \times I_{F(AV)} + 0.0062 I_{F(RMS)}^2$$

DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions			Min.	Typ.	Max.	Unit
trr	I _F = 0.5 A	I _{rr} = 0.25 A	I _R = 1 A	T _j = 25°C		50	ns
	I _F = 1 A	dI _F /dt = - 50 A/μs	V _R = 30 V			60	
I _{RM}	V _{CC} = 200 V I _F = 40 A dI _F /dt = -200 A/μs			T _j = 125°C		13	A
S _{factor}						0.3	-
tfr	I _F = 40 A dI _F /dt = 200 A/μs,			T _j = 25°C		450	ns
V _{FP}	V _{FR} = 1.1 x V _F max					5	

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Fig. 1: Conduction losses versus average current (per diode)

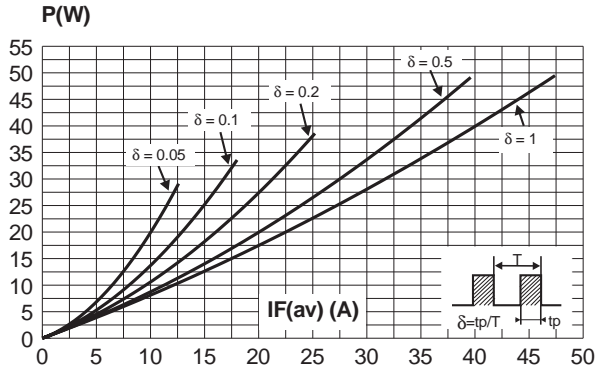


Fig. 2: Forward voltage drop versus forward current (per diode)

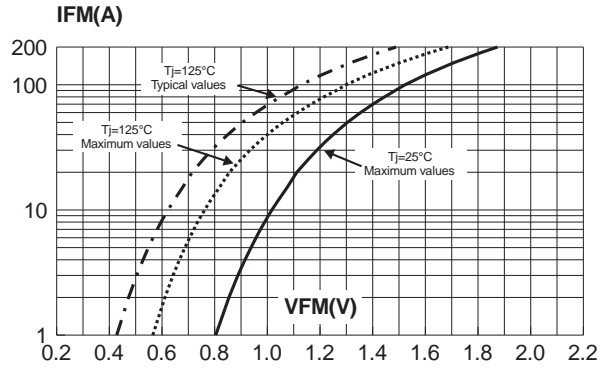


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration

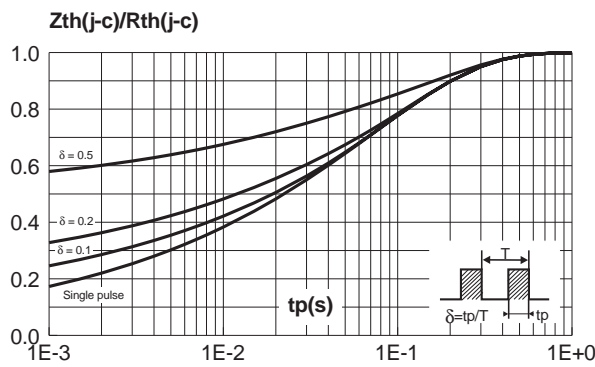


Fig. 4: Peak reverse recovery current versus dIF/dt (90% confidence, per diode)

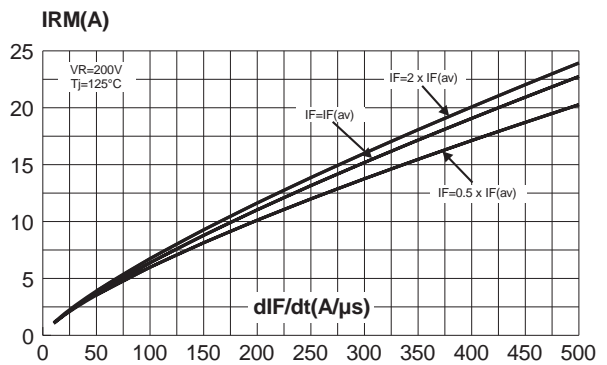


Fig. 5: Reverse recovery time versus dIF/dt (90% confidence, per diode)

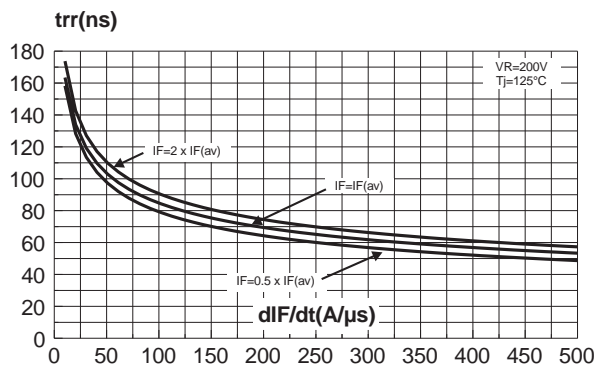
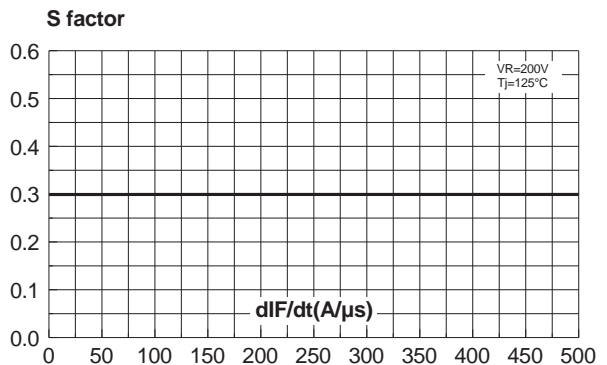


Fig. 6: Softness factor (tb/ta) versus dIF/dt (typical values, per diode)



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Fig. 7: Relative variation of dynamic parameters versus junction temperature (Reference: $T_j = 125^\circ\text{C}$)

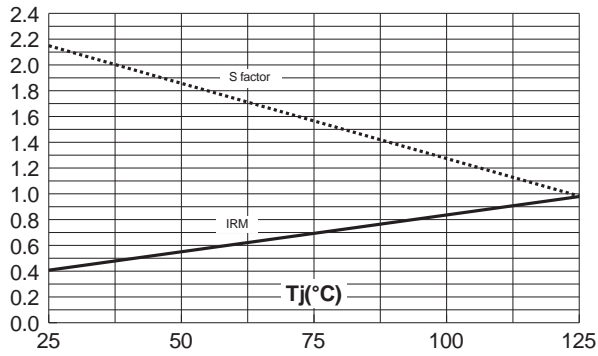


Fig. 8: Transient peak forward voltage versus dI/dt (90% confidence, per diode)

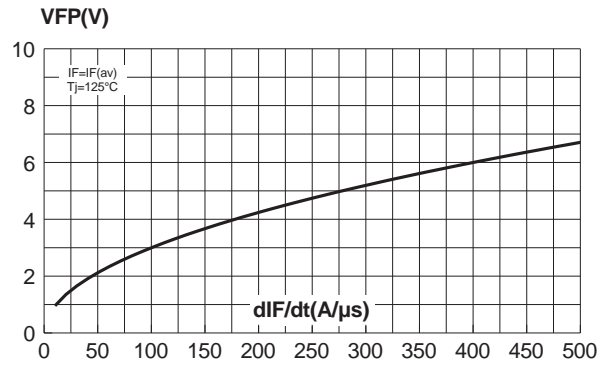
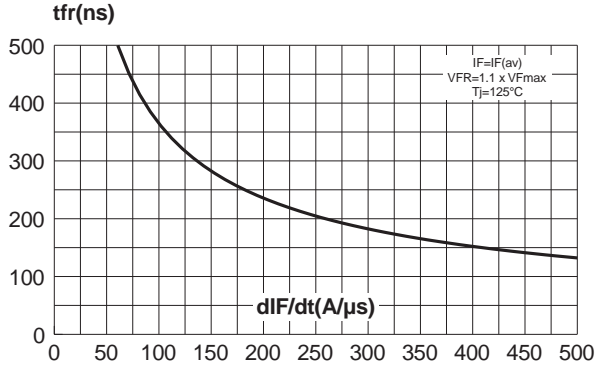


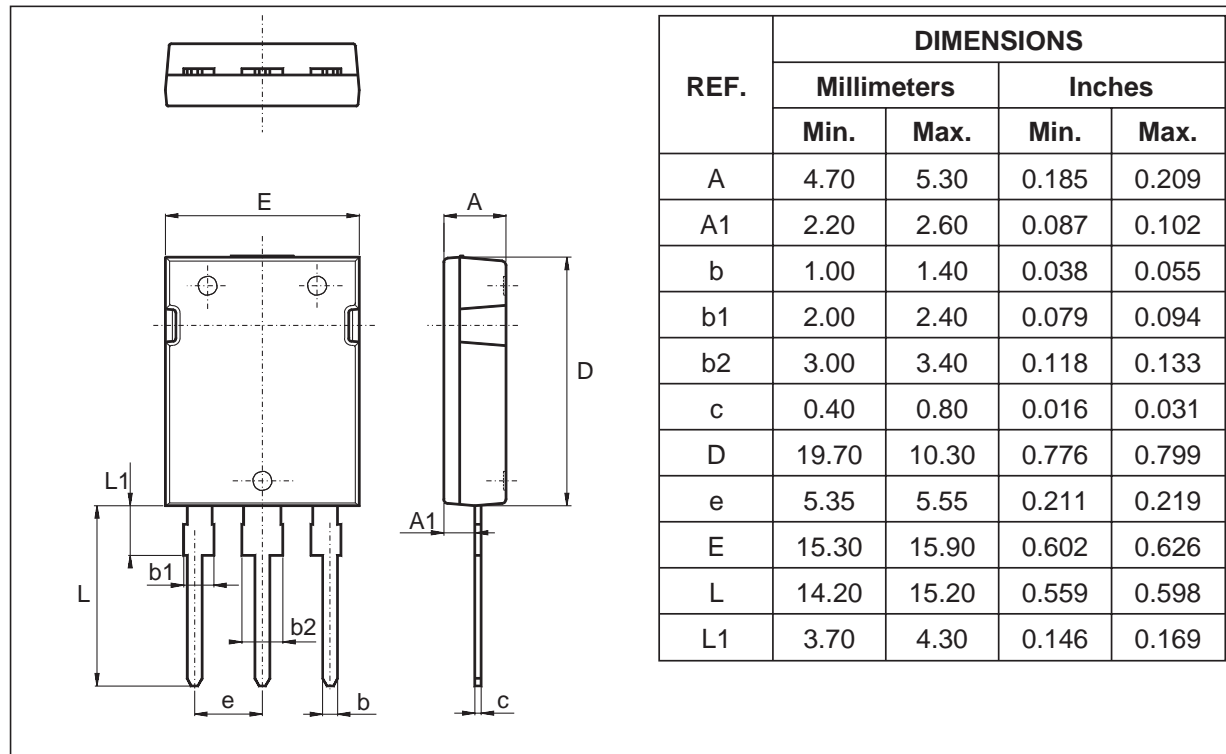
Fig. 9: Forward recovery time versus dI/dt (90% confidence, per diode)



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PACKAGE MECHANICAL DATA

Max247



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH8003CY	STTH8003CY	Max247	4.4 g.	30	Tube

- Cooling method: C
- Epoxy meets UL94,V0

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